

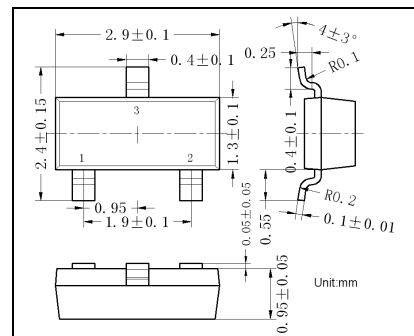
SOT-23 Plastic-Encapsulate Diodes

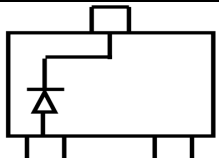
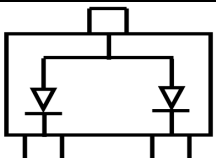
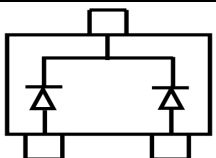
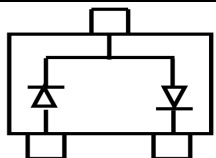
BAS21/A/C/S

Switching Diode

Features

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications
- High Conductance



BAS21	BAS21A	BAS21C	BAS21S
			
Marking: JS	Marking: JS2	Marking: JS3	Marking: JS4

Maximum Ratings ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM} V_{RWM} V_R	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC blocking voltage	250	V
I_{FM}	Forward Continuous Current	400	mA
I_o	Average rectified output current	200	mA
I_{FSM}	Non-Repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	2.5	A
I_{FRM}	Repetitive peak forward surge current	625	mA
P_D	Power Dissipation	225	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	555	$^{\circ}\text{C/W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55 ~ +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)}$	Reverse breakdown voltage	$I_R = 100\mu\text{A}$	250			V
V_F	Forward voltage	$I_F = 100\text{mA}$			1.00	V
		$I_F = 200\text{mA}$			1.25	V
I_R	Reverse voltage leakage current	$V_R = 200\text{V}$			0.1	μA
C_D	Diode capacitance	$V_R = 0, f = 1\text{MHz}$			5	pF
t_{rr}	Reverse recovery time	$I_F = I_R = 30\text{mA}, I_{rr} = 0.1 \times I_R$ $R_L = 100\Omega$			50	ns

Typical Characteristics

